AMENDMENTS TO THE ABSTRACT:

At page 12 (to be added), line 1, please add the following heading and paragraph:

ABSTRACT OF THE DISCLOSURE

A method is disclosed that permits the generation of exclusive high-contrast images of semiconductor sites in an integrated circuit sample (19). It utilizes the one-photon optical beam-induced current (1P-OBIC) image and confocal reflectance image of the sample that are generated simultaneously from one and the same excitation (probe) light beam that is focused on the sample (19). A 1P-OBIC image is a two-dimensional map of the currents induced by the beam as it is scanned across the circuit surface. 1P-OBIC is produced by an illuminated semiconductor material if the excitation photon energy exceeds the bandgap. The 1P-OBIC image has no vertical resolution because 1P-OBIC is linear with the excitation beam intensity. The exclusive high-contrast image of semiconductor sites is generated by the product of the 1P-OBIC image and the confocal image. High-contrast image of the metal sites are also obtained by the product of the complementary OBIC image and the same confocal image.